



**2SB778**

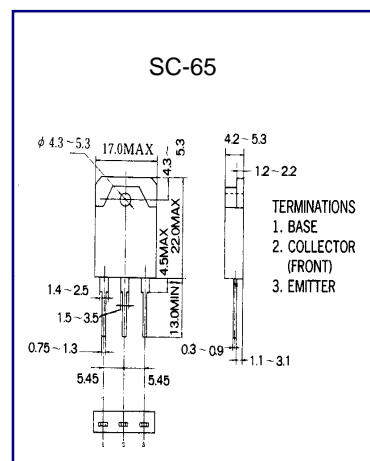
**PNP PLANAR SILICON TRANSISTOR**

**AUDIO POWER AMPLIFIER  
DC TO DC CONVERTER**

- High Current Capability
- High Power Dissipation

**ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-120	V
Emitter-Base voltage	V <sub>EB0</sub>	-6	V
Collector Current (DC)	I <sub>C</sub>	-10	A
Collector Dissipation	P <sub>C</sub>	80	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV <sub>CB0</sub>	I <sub>C</sub> =-5 mA I <sub>E</sub> =0	-120			V
Collector Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =-10 mA R <sub>BE</sub> =∞	-120			V
Emitter Base Breakdown Voltage	BV <sub>EB0</sub>	I <sub>E</sub> =-5mA I <sub>C</sub> =0	-6			V
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =-60V I <sub>E</sub> =0			-0.1	mA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> =-4V I <sub>C</sub> =0			-0.1	mA
*DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> =-5V I <sub>C</sub> =-1A	55	120	160	
DC Current Gain	h <sub>FE2</sub>	V <sub>CE</sub> =-5V I <sub>C</sub> =-2A				
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-3A I <sub>B</sub> =-0.3A			-1.5	V